

Application No. 09/768,912

IN THE CLAIMS

1 - 8. (Canceled)

9. (Currently amended) A semiconductor device comprising:

a single-crystal substrate made of a material different from nitride III-V compound semiconductors, said substrate extending between a first surface and a second surface opposite said first surface and having a hole extending through the substrate from said first surface to said second surface;

a device formed on one of said first and second surfaces of said single-crystal substrate using III-V compound semiconductors;

a layer disposed on one of said first and second surfaces of said single-crystal substrate, wherein said hole extends to said layer;

wherein said device is formed between said layer and said substrate and is electrically connected to said layer; and

wherein an electrical connection to said device is created via the hole extending through the substrate and contact with said layer.

10. (Previously presented) The semiconductor device according to claim 9, wherein said single-crystal substrate comprises a material selected from a group consisting of sapphire, spinel, perovskite yttrium aluminate, and SiC.

11. (Previously presented) The semiconductor device according to claim 9 wherein said semiconductor device comprises a semiconductor laser using nitride III-V compound semiconductors.

12. (Previously presented) The semiconductor device according to claim 9 wherein said semiconductor device comprises an FET using nitride III-V compound semiconductors.

13 - 24. (Canceled)

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25. (Currently amended) A semiconductor device comprising:

a single-crystal substrate made of a material different from nitride III-V compound semiconductors, said substrate extending between a first surface and a second surface opposite said first surface and having a hole extending through the substrate from said first surface to said second surface;

a device formed on one of said first and second surfaces of said single-crystal substrate using III-V compound semiconductors;

a layer disposed on one of said first and second surfaces of said single-crystal substrate and electrically connected to said device, said layer having a first side facing the substrate and a second side opposite the first side and facing away from the substrate, wherein said hole extends to said layer;

wherein a surface of the layer device facing the substrate is at least as close to the substrate as ~~a surface of the device~~ the second side of the layer facing away from the substrate; and

wherein an electrical connection to said device is created via the hole extending through the substrate and contact with said layer.